

Fig.1 C-V characteristics of (a) as-deposited and (b) 900°C annealed sample of the structure ALD- $\text{Al}_2\text{O}_3/\text{ALD-Y}_2\text{O}_3/p\text{-GaAs}(001)$

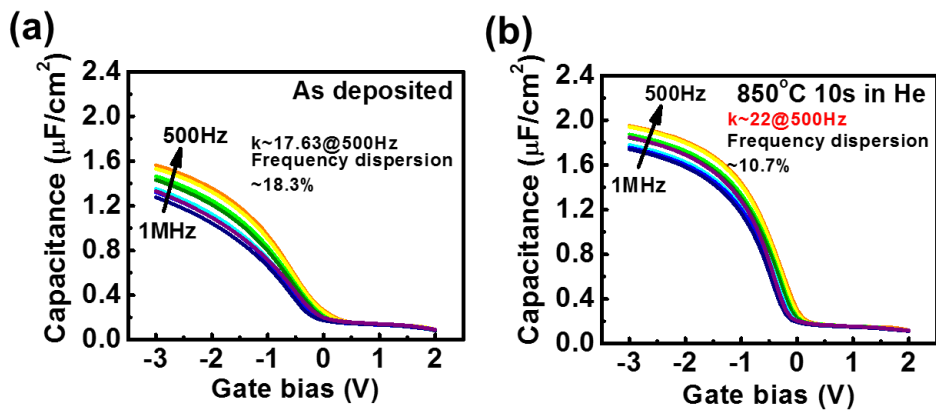


Fig.2 C-V characteristics of (a) as-deposited and (b) 850°C annealed sample of the structure ALD- $\text{HfAlO}/\text{ALD-HfO}_2/p\text{-GaAs}(001)$

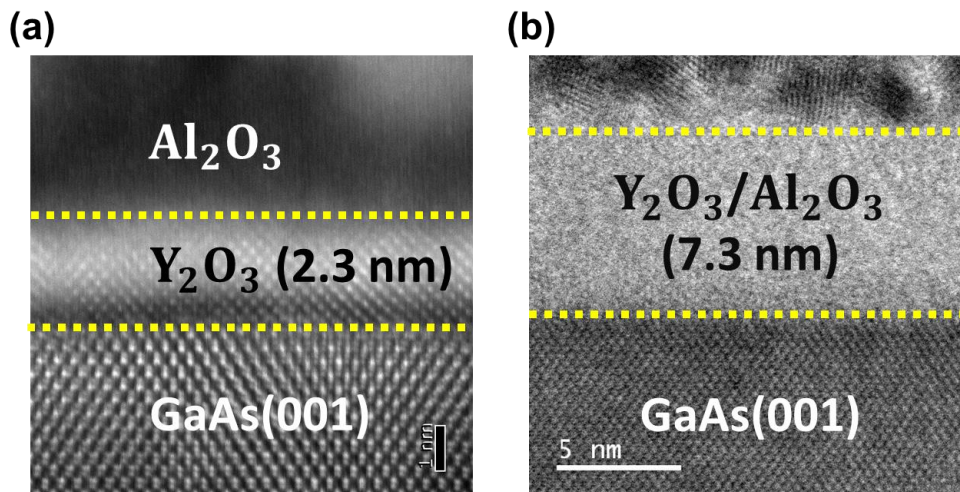


Fig. 3 STEM images for $\text{Y}_2\text{O}_3/\text{Al}_2\text{O}_3$ gate stack on GaAs(001) (a) as-deposited, and (b) with annealing at 900°C in He